

# KA5M0965Q

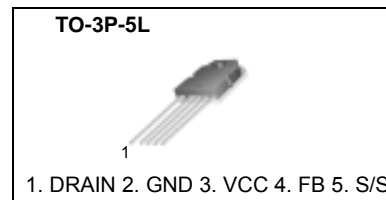
## Fairchild Power Switch(FPS)

### Features

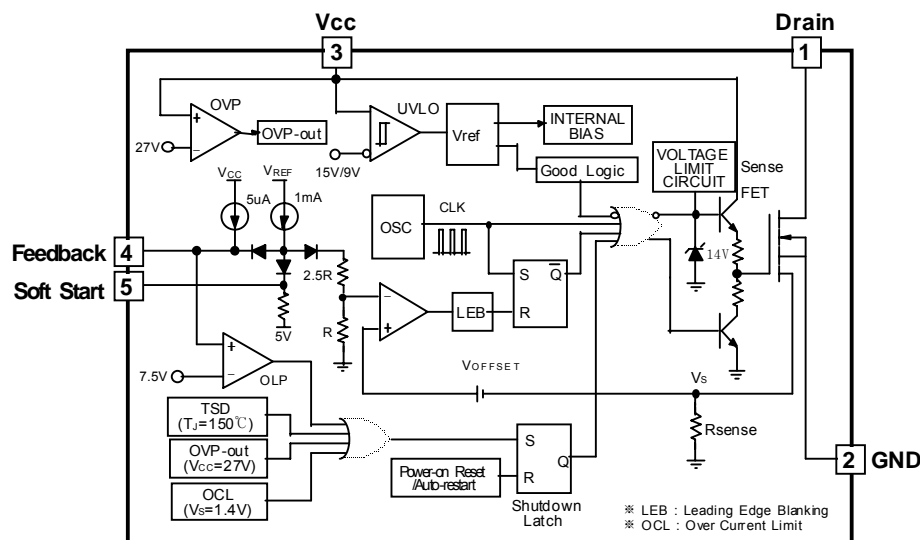
- Precision Fixed Operating Frequency (70kHz)
- Low Start-up Current(Typ. 100uA)
- Pulse by Pulse Current Limiting
- Over Load Protection
- Over Current Protection
- Over Voltage Protection (Min. 25V)
- Internal Thermal Shutdown Function
- Under Voltage Lockout
- Internal High Voltage Sense FET
- Latch Mode

### Description

The Fairchild Power Switch(FPS) product family is specially designed for an off-line SMPS with minimal external components. The Fairchild Power Switch(FPS) consist of high voltage power SenseFET and current mode PWM IC. Included PWM controller features integrated fixed frequency oscillator, under voltage lock-out, leading edge blanking, optimized gate turn-on/turn-off driver, thermal shutdown protection, over voltage protection, and temperature compensated precision current sources for loop compensation and fault protection circuitry. compared to discrete MOSFET and PWM controller or RCC solution, a Fairchild Power Switch(FPS) can reduce total component count, design size, weight and at the same time increase efficiency, productivity, and system reliability. It has a basic platform well suited for cost effective design in either a flyback converter or a forward converter.



### Internal Block Diagram



Rev.1.0.3

## Absolute Maximum Ratings

Characteristic	Symbol	Value	Unit
Drain-Gate Voltage (R <sub>GS</sub> =1MΩ)	V <sub>DGR</sub>	650	V
Gate-Source (GND) Voltage	V <sub>GS</sub>	±30	V
Drain Current Pulsed <sup>(2)</sup>	I <sub>DM</sub>	36.0	ADC
Single Pulsed Avalanche Energy <sup>(3)</sup>	E <sub>AS</sub>	950	mJ
Continuous Drain Current (T <sub>C</sub> =25°C)	I <sub>D</sub>	9.0	ADC
Continuous Drain Current (T <sub>C</sub> =100°C)	I <sub>D</sub>	5.8	ADC
Maximum Supply Voltage	V <sub>CC,MAX</sub>	30	V
Input Voltage Range	V <sub>FB</sub>	-0.3 to V <sub>SD</sub>	V
Total Power Dissipation	P <sub>D</sub> (watt H/S)	170	W
	Darting	1.33	W/°C
Operating Ambient Temperature	T <sub>A</sub>	-25 to +85	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C

**Note:**

1. T<sub>j</sub> = 25°C to 150°C
2. Repetitive rating: Pulse width limited by maximum junction temperature
3. L = 20mH, V<sub>DD</sub> = 50V, R<sub>G</sub> = 27Ω, starting T<sub>j</sub> = 25°C

## Electrical Characteristics (SFET Part)

(Ta = 25°C unless otherwise specified)

Characteristic	Symbol	Test condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =50μA	650	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =Max., Rating, V <sub>GS</sub> =0V	-	-	50	μA
		V <sub>DS</sub> =0.8Max., Rating, V <sub>GS</sub> =0V, T <sub>C</sub> =125°C	-	-	200	mA
Static Drain-Source on Resistance <sup>(Note)</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =4.5A	-	0.96	1.2	W
Forward Transconductance <sup>(Note)</sup>	g <sub>fs</sub>	V <sub>DS</sub> =50V, I <sub>D</sub> =4.5A	5.0	-	-	S
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz	-	1200	-	pF
Output Capacitance	C <sub>oss</sub>		-	135	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	25	-	
Turn on Delay Time	td(on)	V <sub>DD</sub> =0.5BV <sub>DSS</sub> , I <sub>D</sub> =9.0A (MOSFET switching time are essentially independent of operating temperature)	-	25	60	nS
Rise Time	tr		-	75	160	
Turn Off Delay Time	td(off)		-	130	270	
Fall Time	tf		-	70	150	
Total Gate Charge (Gate-Source+Gate-Drain)	Q <sub>g</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =9.0A, V <sub>DS</sub> =0.8BV <sub>DSS</sub>	-	45	60	nC
Gate-Source Charge	Q <sub>gs</sub>		-	8	-	
Gate-Drain (Miller) Charge	Q <sub>gd</sub>		-	22	-	

**Note:**

1. Pulse test: Pulse width ≤ 300μS, duty ≤ 2%
2.  $S = \frac{1}{R}$

**Electrical Characteristics (Control Part)** (Continued)

(Ta = 25°C unless otherwise specified)

Characteristic	Symbol	Test condition	Min.	Typ.	Max.	Unit
<b>UVLO SECTION</b>						
Start Threshold Voltage	VSTART	-	14	15	16	V
Stop Threshold Voltage	VSTOP	After turn on	8.4	9	9.6	V
<b>OSCILLATOR SECTION</b>						
Initial Accuracy	FOSC	Ta=25°C	61	67	73	kHz
Frequency Change With Temperature <sup>(2)</sup>	-	-25°C ≤ Ta ≤ +85°C	-	±5	±10	%
Maximum Duty Cycle	Dmax	-	74	77	80	%
<b>FEEDBACK SECTION</b>						
Feedback Source Current	I <sub>FB</sub>	Ta=25°C, 0V ≤ V <sub>fb</sub> ≤ 3V	0.7	0.9	1.1	mA
Shutdown Feedback Voltage	VSD	V <sub>fb</sub> ≥ 6.5V	6.9	7.5	8.1	V
Shutdown Delay Current	I <sub>delay</sub>	Ta=25°C, 5V ≤ V <sub>fb</sub> ≤ VSD	4	5	6	μA
<b>SOFT START SECTION</b>						
Soft Start Voltage	V <sub>SS</sub>	V <sub>FB</sub> = 2V	4.7	5.0	5.3	V
Soft Start Current	I <sub>SS</sub>	Sync & S/S=GND	0.8	1.0	1.2	mA
<b>CURRENT LIMIT(SELF-PROTECTION)SECTION</b>						
Peak Current Limit	I <sub>OVER</sub>	Max. inductor current	5.28	6.00	6.72	A
<b>PROTECTION SECTION</b>						
Thermal Shutdown Temperature (T <sub>j</sub> ) <sup>(1)</sup>	T <sub>SD</sub>	-	140	160	-	°C
Over Voltage Protection Voltage	VOVP	V <sub>CC</sub> ≥ 24V	25	27	29	V
<b>TOTAL DEVICE SECTION</b>						
Start-up Current	I <sub>START</sub>	V <sub>CC</sub> =14V	-	0.1	0.17	mA
Operating Supply Current (Control Part Only)	I <sub>OP</sub>	V <sub>CC</sub> ≤ 28	-	7	12	mA

**Note:**

1. These parameters, although guaranteed, are not 100% tested in production
2. These parameters, although guaranteed, are tested in EDS(water test) process
3. These parameters are indicated Inductor current.

## Typical Performance Characteristics

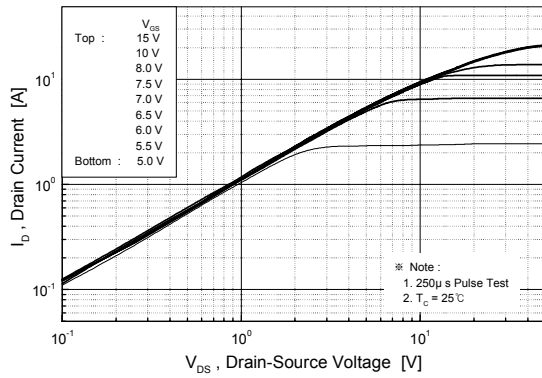


Figure 1. Output Characteristics

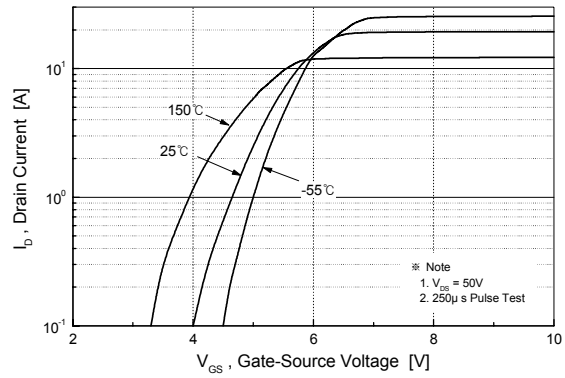


Figure 2. Transfer Characteristics

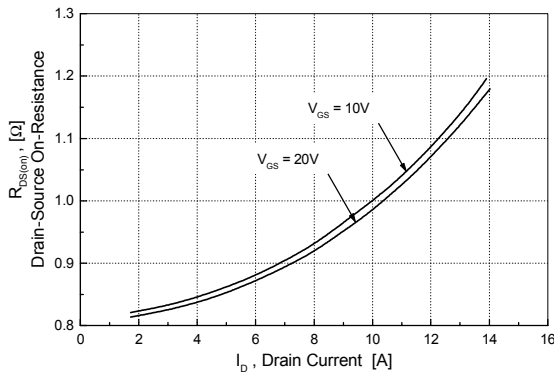


Figure 3. On-Resistance vs. Drain Current

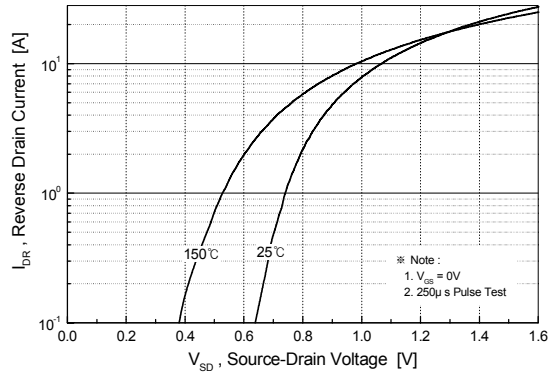


Figure 4. Source-Drain Diode Forward Voltage

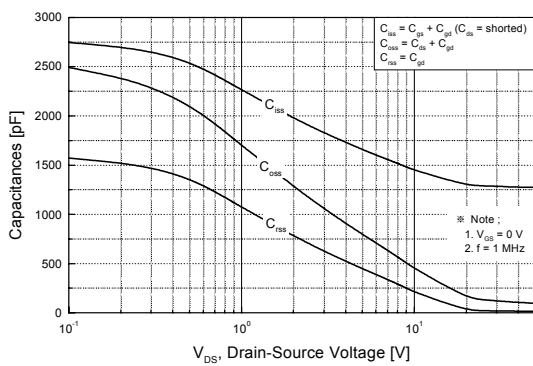


Figure 5. Capacitance vs. Drain-Source Voltage

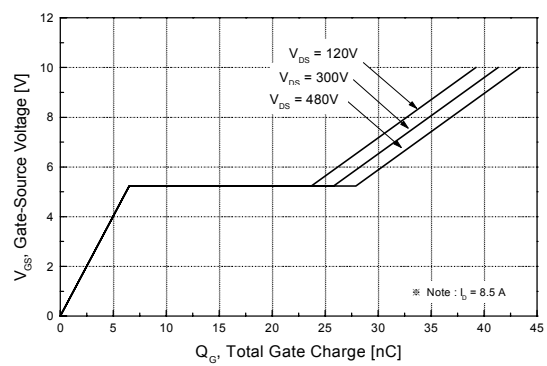


Figure 6. Gate Charge vs. Gate-Source Voltage

Typical Performance Characteristics (Continued)

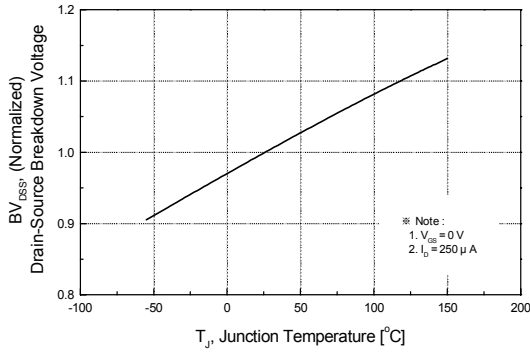


Figure 7. Breakdown Voltage vs. Temperature

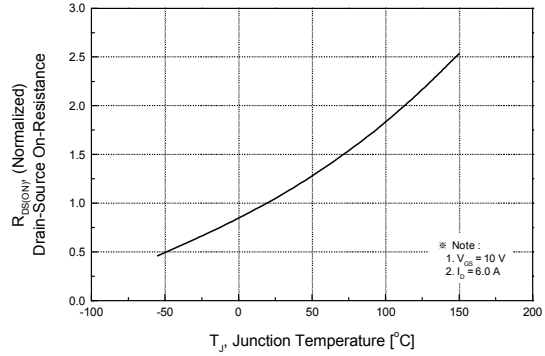


Figure 8. On-Resistance vs. Temperature

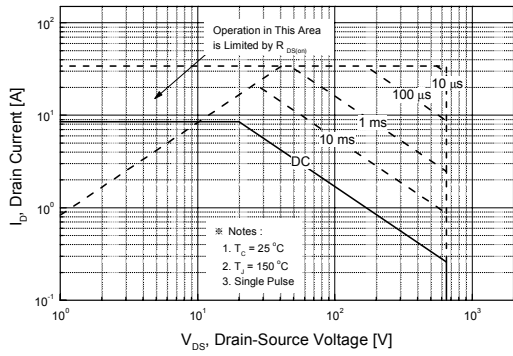


Figure 9. Max. Safe Operating Area

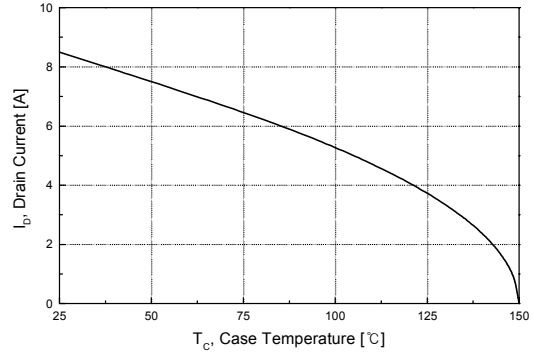


Figure 10. Max. Drain Current vs. Case Temperature

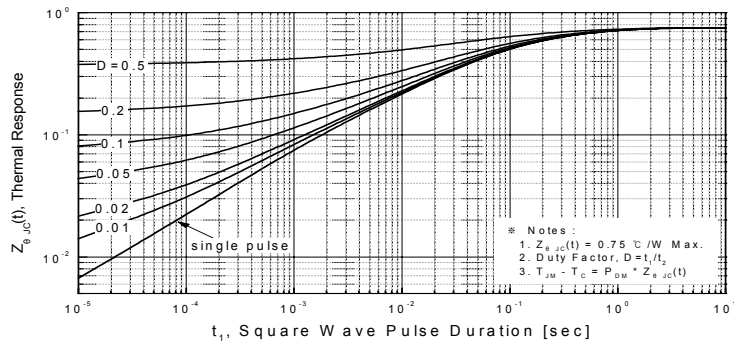


Figure 11. Thermal Response

## Typical Performance Characteristics (Control part) (Continued)

(These characteristic graphs are normalized at  $T_a = 25^\circ\text{C}$ )

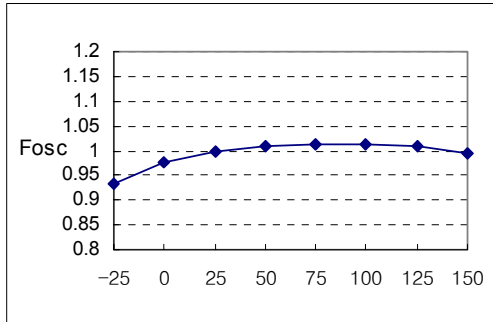


Figure 1. Operating Frequency

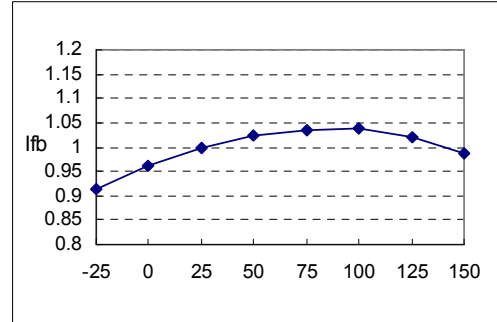


Figure 2. Feedback Source Current

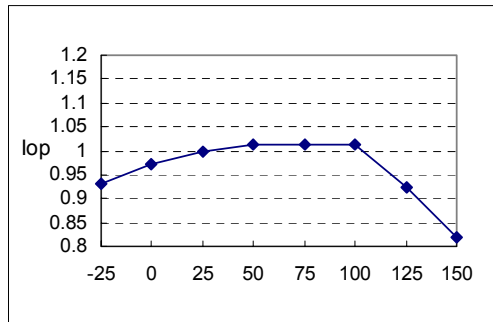


Figure 3. Operating Supply Current

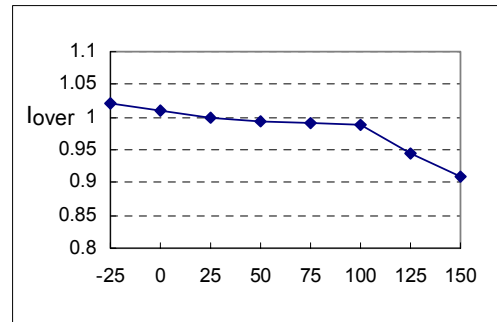


Figure 4. Peak Current Limit

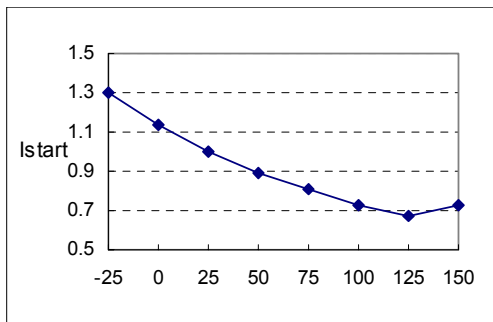


Figure 5. Start up Current

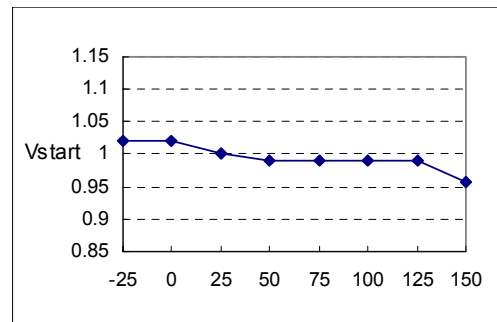
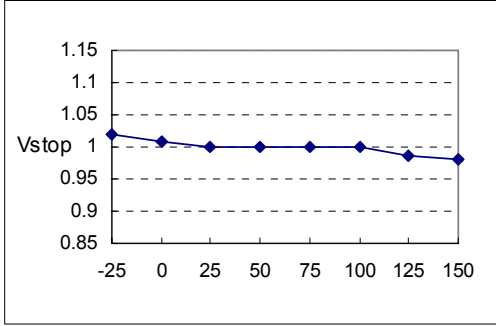


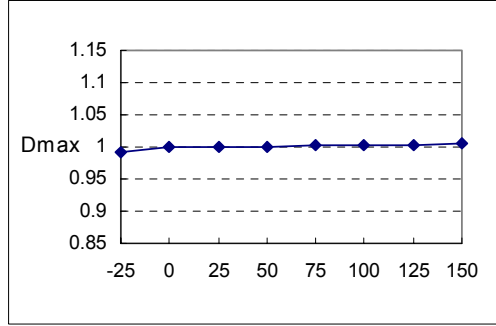
Figure 6. Start Threshold Voltage

**Typical Performance Characteristics** (Continued)

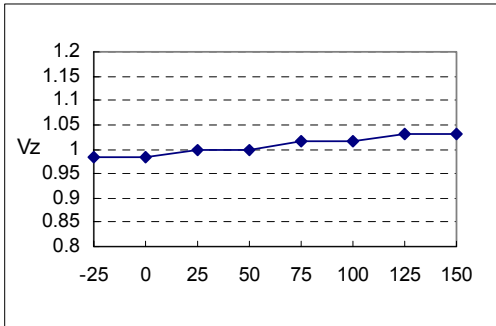
(These characteristic graphs are normalized at  $T_a = 25^\circ\text{C}$ )



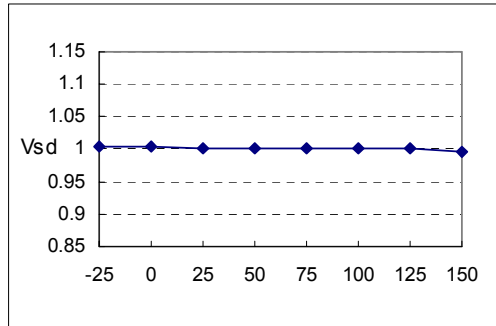
**Figure 7. Stop Threshold Voltage**



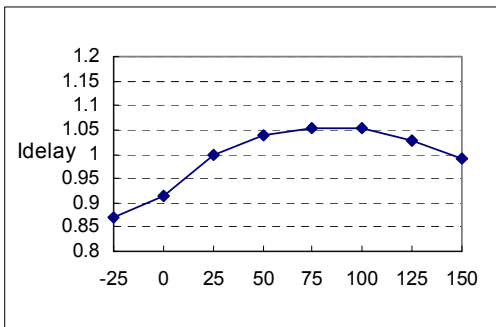
**Figure 8. Maximum Duty Cycle**



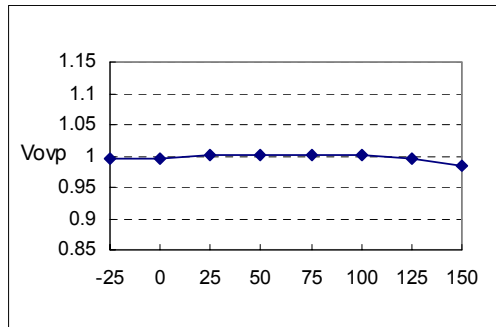
**Figure 9. VCC Zener Voltage**



**Figure 10. Shutdown Feedback Voltage**



**Figure 11. Shutdown Delay Current**



**Figure 12. Over Voltage Protection**



## Typical Performance Characteristics (Continued)

(These characteristic graphs are normalized at  $T_a = 25^\circ\text{C}$ )

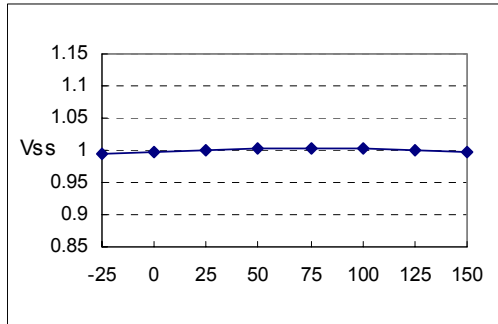


Figure13. Soft Start Voltage

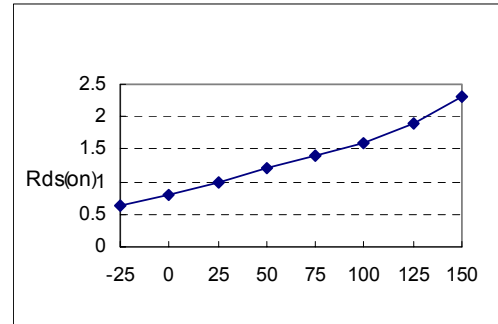
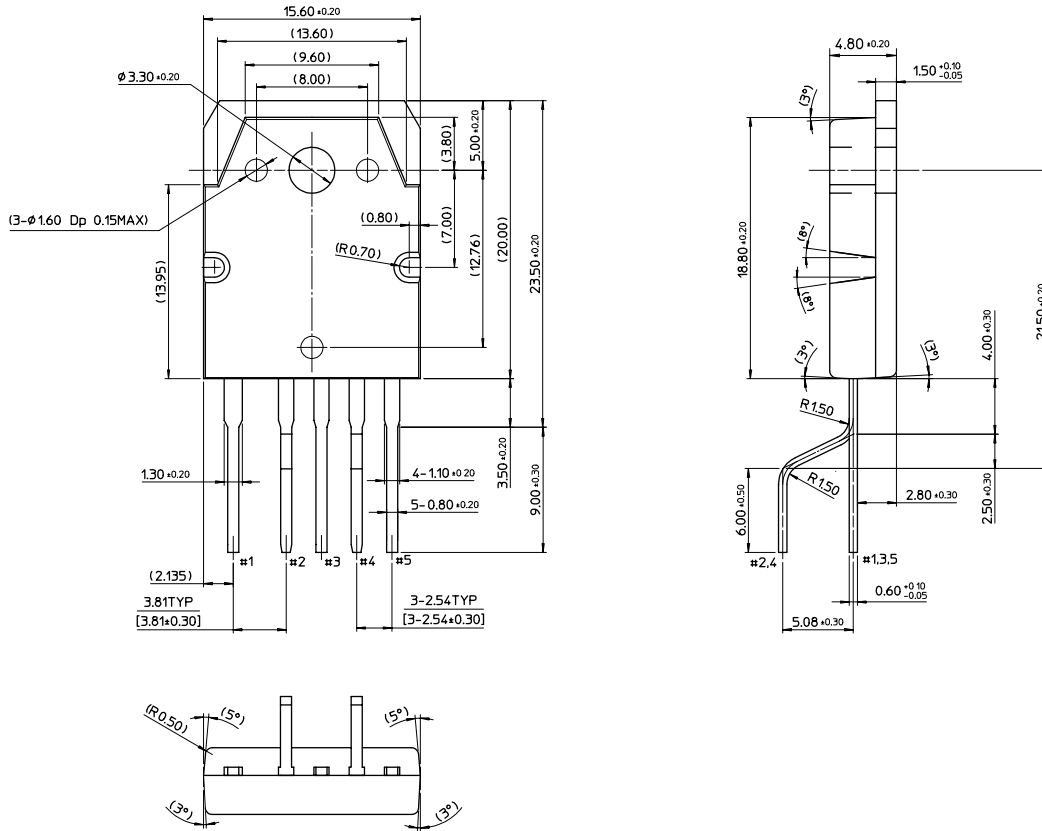


Figure 14. Static Drain-Source on Resistance



Package Dimensions (Continued)

TO-3P-5L (Forming)



## Ordering Information

Product Number	Package	Rating	Operating Temperature
KA5M0965QTU	TO-3P-5L	650V, 9A	-25°C to +85°C
KA5M0965QYDTU	TO-3P-5L(Forming)		

TU : Non Forming Type

YDTU : Forming Type

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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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